

# 2N7002BKS

60 V, 300 mA dual N-channel Trench MOSFET

Rev. 2 — 23 September 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

### 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

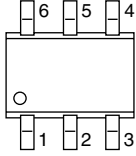
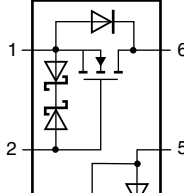
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	-	60	V
$V_{GS}$	gate-source voltage	$T_{amb} = 25\text{ °C}$	-	-	$\pm 20$	V
$I_D$	drain current	$T_{amb} = 25\text{ °C};$ $V_{GS} = 10\text{ V}$	[1] -	-	300	mA
$R_{DS(on)}$	drain-source on-state resistance	$T_j = 25\text{ °C};$ $V_{GS} = 10\text{ V};$ $I_D = 500\text{ mA}$	-	1	1.6	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



## 2. Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		
2	G1	gate 1		
3	D2	drain 2		
4	S2	source 2		
5	G2	gate 2		
6	D1	drain 1		

017aaa055

## 3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
2N7002BKS	SC-88	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
2N7002BKS	ZT*

- [1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Per transistor</b>					
$V_{DS}$	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	60	V
$V_{GS}$	gate-source voltage	$T_{amb} = 25\text{ °C}$	-	±20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$	[1]		
		$T_{amb} = 25\text{ °C}$	-	300	mA
		$T_{amb} = 100\text{ °C}$	-	215	mA

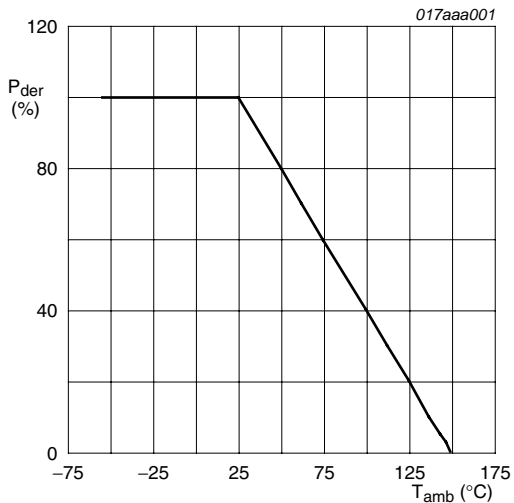
**Table 5. Limiting values ...continued**  
 In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs	-	1.2	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] -	295	mW
			[1] -	340	mW
		T <sub>sp</sub> = 25 °C	-	1040	mW
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1] -	300	mA
<b>ESD maximum rating</b>					
V <sub>ESD</sub>	electrostatic discharge voltage	human body model	[3] -	2000	V
<b>Per device</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] -	445	mW
T <sub>j</sub>	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

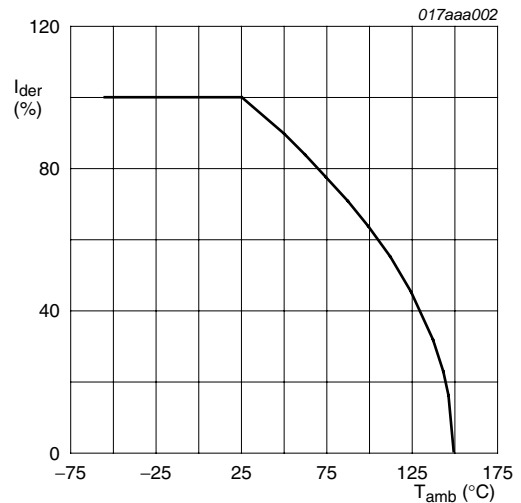
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



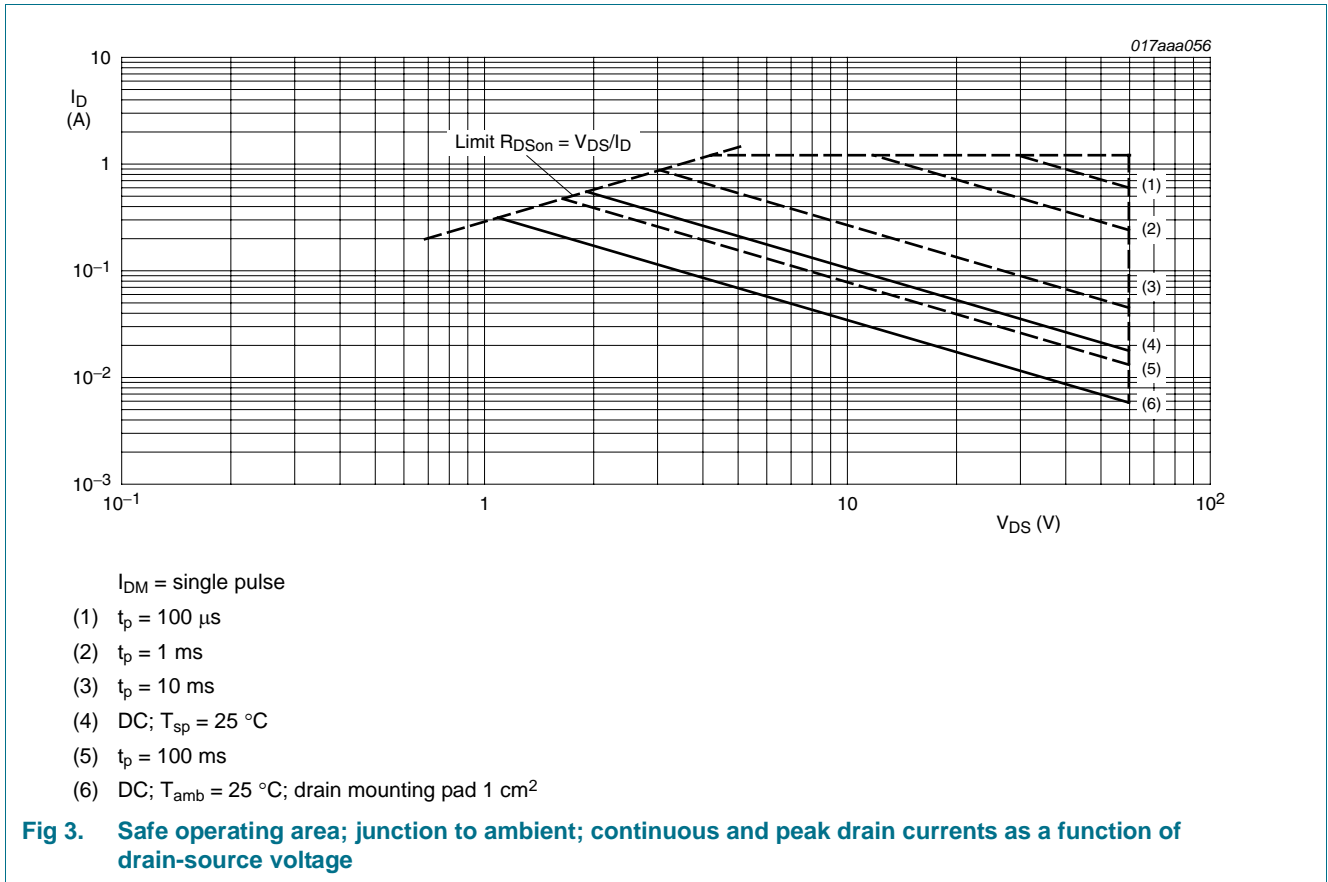
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of ambient temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of ambient temperature**



## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	370	425 K/W
			[2]	-	320	370 K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	120	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	275 K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $1 \text{ cm}^2$ .

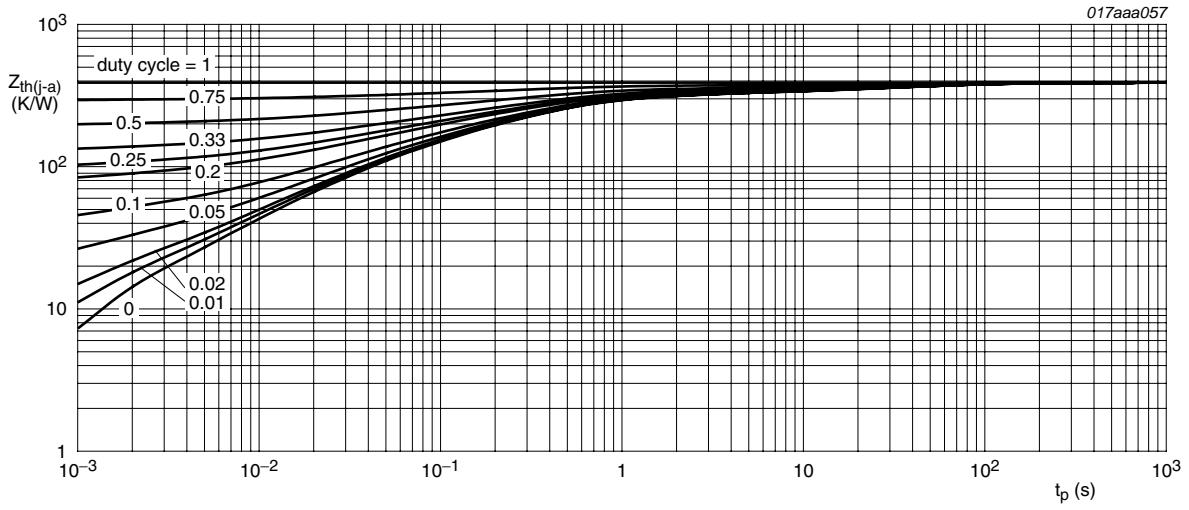


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

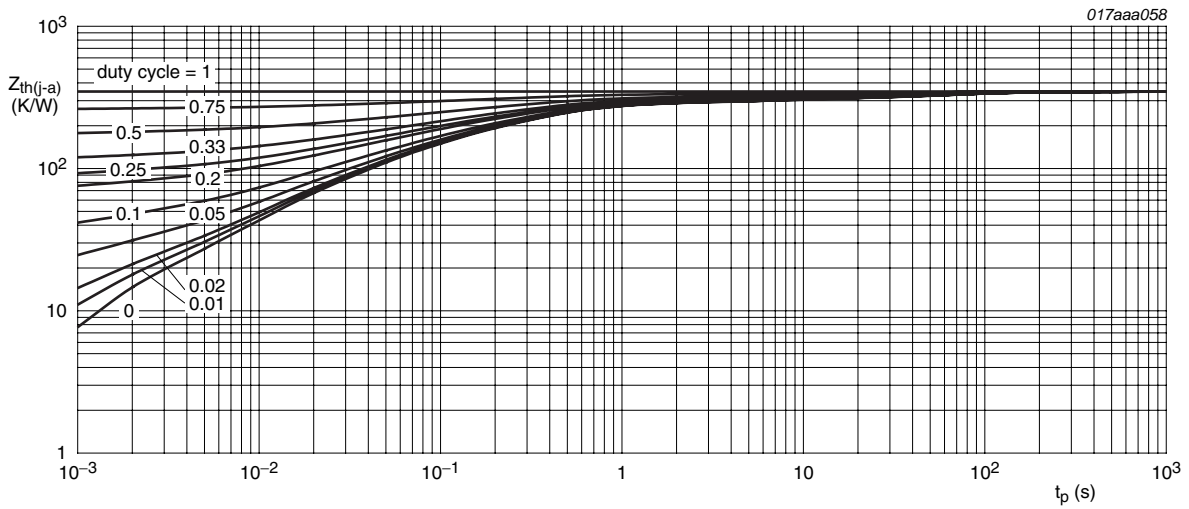


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

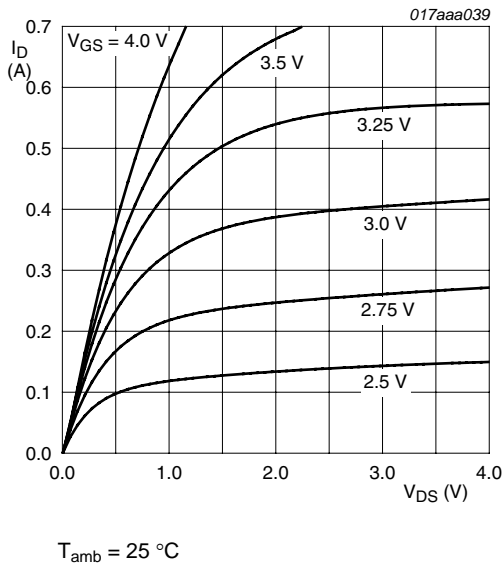
## 7. Characteristics

**Table 7. Characteristics**

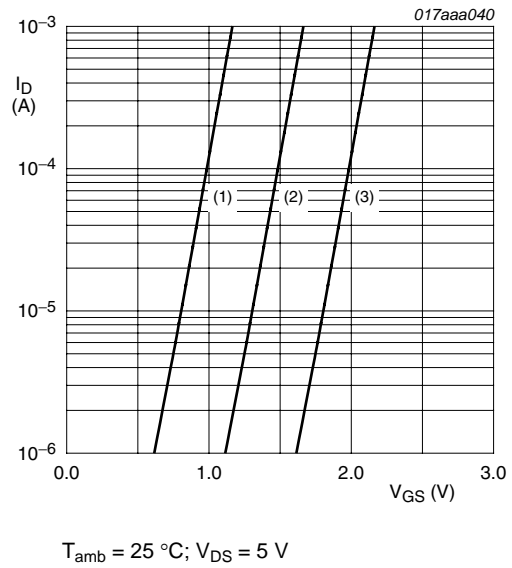
$T_j = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10\ \mu\text{A}; V_{GS} = 0\ \text{V}$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250\ \mu\text{A}; V_{DS} = V_{GS}$	1.1	1.6	2.1	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60\ \text{V}; V_{GS} = 0\ \text{V}$				
		$T_j = 25\text{ °C}$	-	-	1	$\mu\text{A}$
		$T_j = 150\text{ °C}$	-	-	10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = \pm 20\ \text{V}; V_{DS} = 0\ \text{V}$	-	-	10	$\mu\text{A}$
$R_{DS(on)}$	drain-source on-state resistance		[1]			
		$V_{GS} = 5\ \text{V}; I_D = 50\ \text{mA}$	-	1.3	2	$\Omega$
		$V_{GS} = 10\ \text{V}; I_D = 500\ \text{mA}$	-	1	1.6	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10\ \text{V}; I_D = 200\ \text{mA}$	[1]	-	550	mS
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 300\ \text{mA};$ $V_{DS} = 30\ \text{V};$ $V_{GS} = 4.5\ \text{V}$	-	0.5	0.6	nC
$Q_{GS}$	gate-source charge		-	0.2	-	nC
$Q_{GD}$	gate-drain charge		-	0.1	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\ \text{V}; V_{DS} = 10\ \text{V};$ $f = 1\ \text{MHz}$	-	33	50	pF
$C_{oss}$	output capacitance		-	7	-	pF
$C_{rss}$	reverse transfer capacitance		-	4	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 50\ \text{V};$ $R_L = 250\ \Omega;$ $V_{GS} = 10\ \text{V};$ $R_G = 6\ \Omega$	-	5	10	ns
$t_r$	rise time		-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	12	24	ns
$t_f$	fall time		-	7	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 115\ \text{mA}; V_{GS} = 0\ \text{V}$	0.47	0.75	1.1	V

[1] Pulse test:  $t_p \leq 300\ \mu\text{s}; \delta \leq 0.01$ .

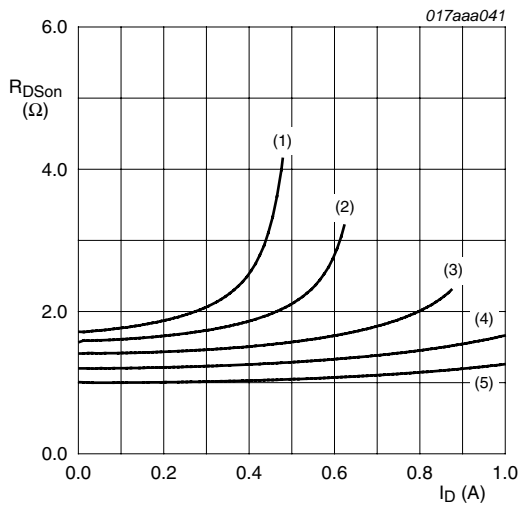


**Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



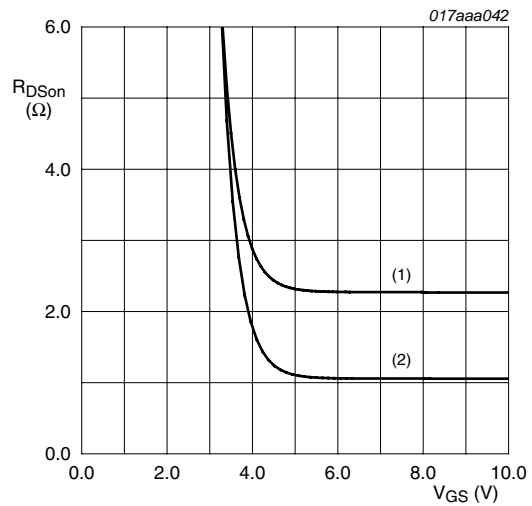
**Fig 7. Sub-threshold drain current as a function of gate-source voltage**

- (1) minimum values
- (2) typical values
- (3) maximum values



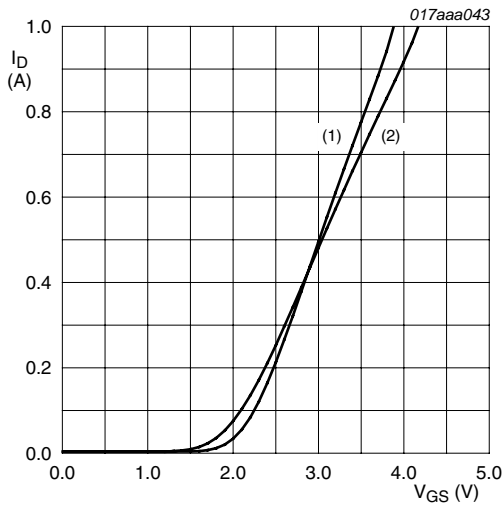
**Fig 8. Drain-source on-state resistance as a function of drain current; typical values**

- $T_{amb} = 25\text{ °C}$
- (1)  $V_{GS} = 3.25\text{ V}$
- (2)  $V_{GS} = 3.5\text{ V}$
- (3)  $V_{GS} = 4\text{ V}$
- (4)  $V_{GS} = 5\text{ V}$
- (5)  $V_{GS} = 10\text{ V}$



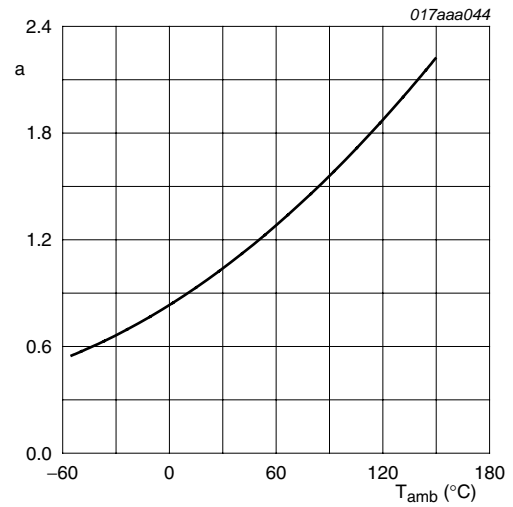
**Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**

- $I_D = 500\text{ mA}$
- (1)  $T_{amb} = 150\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$



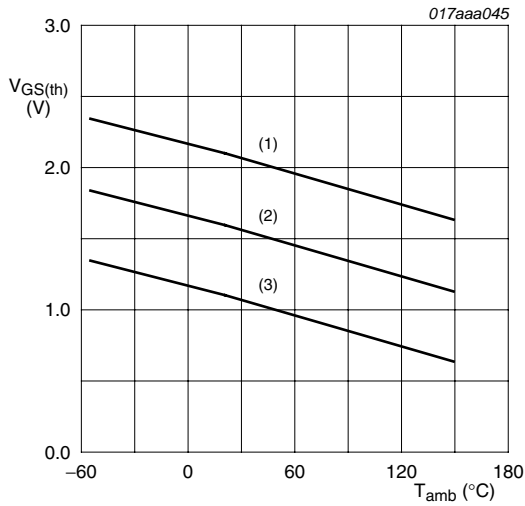
$V_{DS} > I_D \times R_{DSon}$   
 (1)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 150\text{ }^\circ\text{C}$

**Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



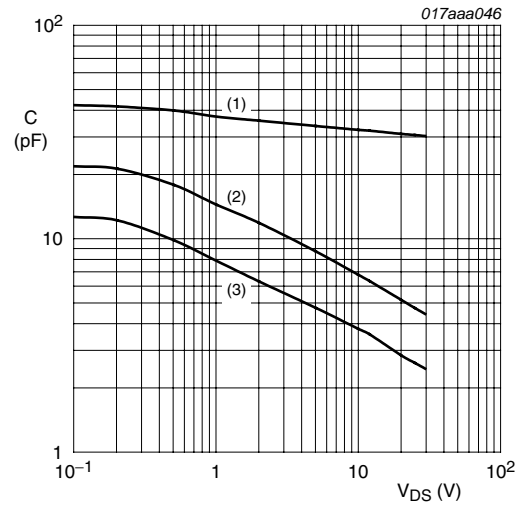
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

**Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values**



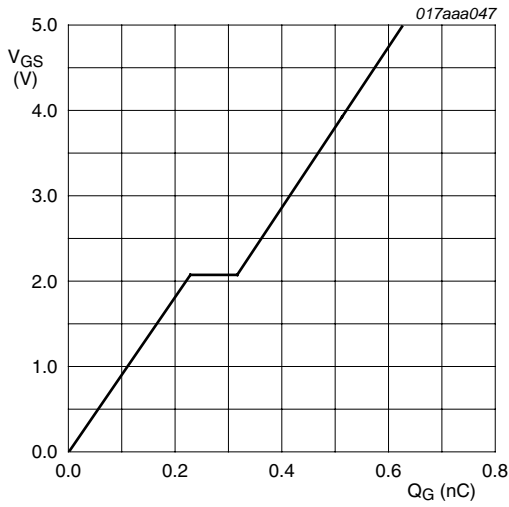
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

**Fig 12. Gate-source threshold voltage as a function of ambient temperature**



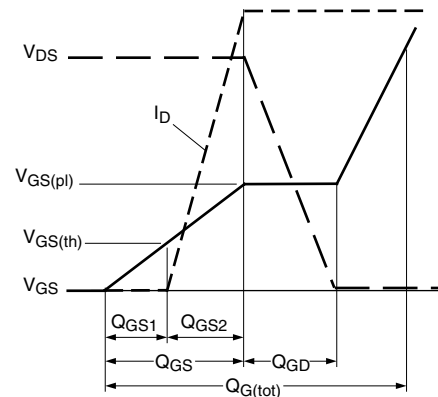
$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

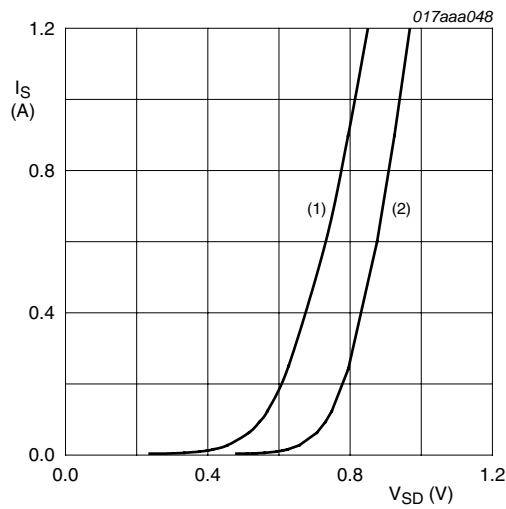


$I_D = 300 \text{ mA}; V_{DD} = 6 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 14. Gate-source voltage as a function of gate charge; typical values**



**Fig 15. Gate charge waveform definitions**

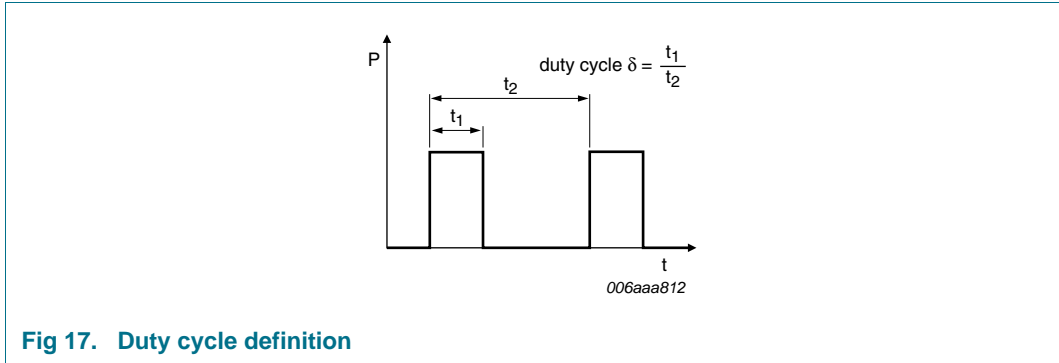


$V_{GS} = 0 \text{ V}$

- (1)  $T_{amb} = 150 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig 16. Source current as a function of source-drain voltage; typical values**

**8. Test information**



9. Package outline

Plastic surface-mounted package; 6 leads

SOT363

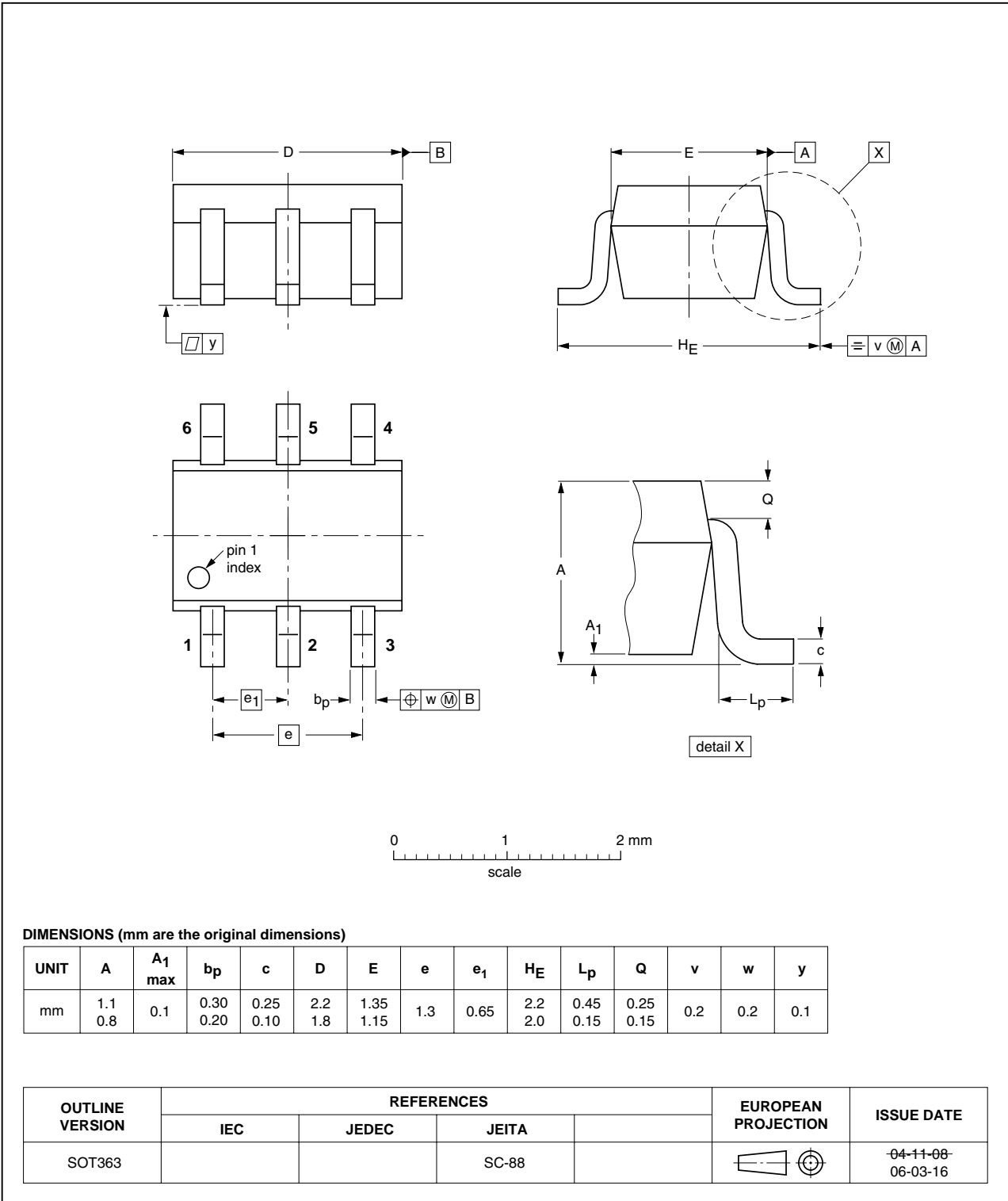


Fig 18. Package outline SOT363 (SC-88)

10. Soldering

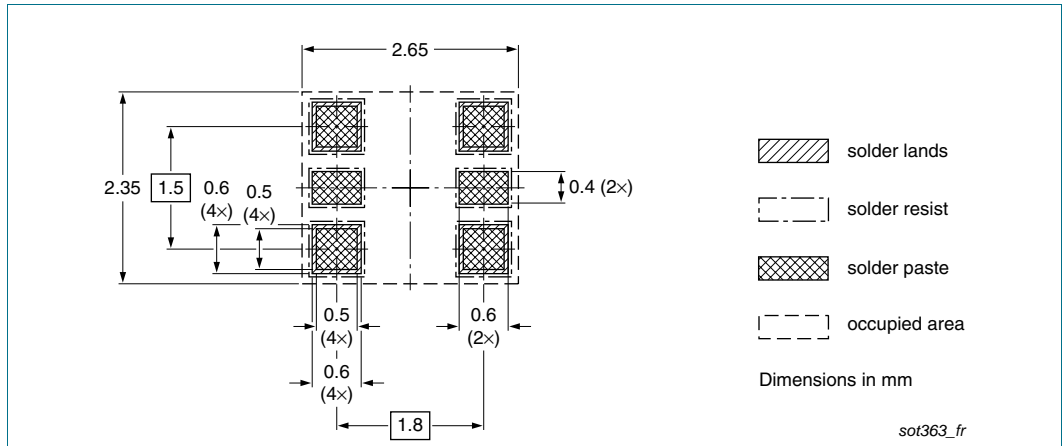


Fig 19. Reflow soldering footprint SOT363 (SC-88)

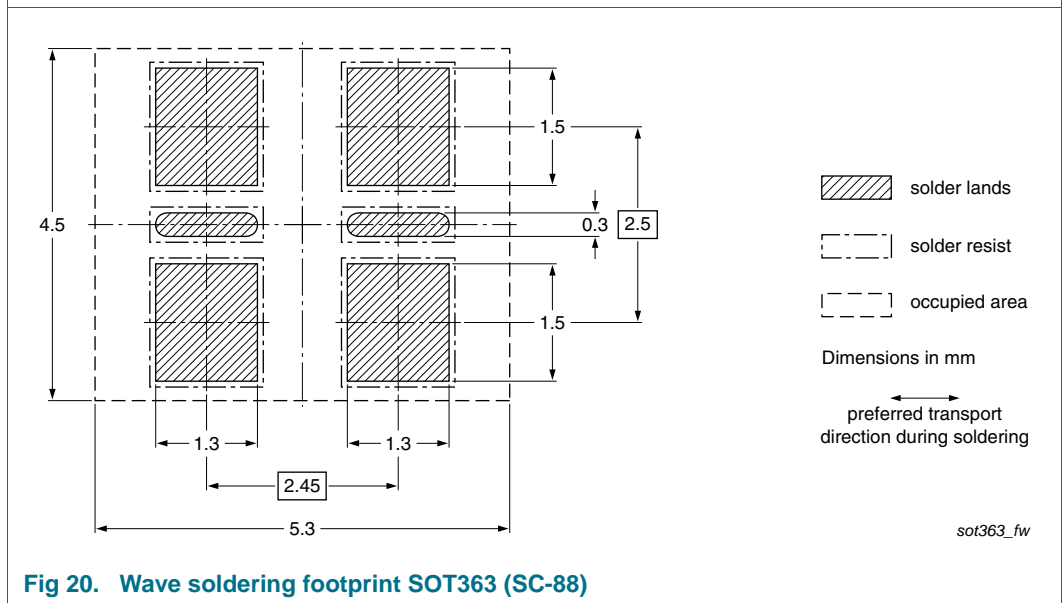


Fig 20. Wave soldering footprint SOT363 (SC-88)

## 11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002BKS v.2	20100923	Product data sheet	-	2N7002BKS v.1
Modifications:	• <a href="#">Table 2 "Pinning"</a> : graphic symbol amended			
2N7002BKS v.1	20100617	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 23 September 2010

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